

Phase Control Thyristors (Hockey PUK Version), 1473 A



A-24 (K-PUK)

PRODUCT SUMMARY					
Package	A-24 (K-PUK)				
Diode variation	Single SCR				
I _{T(AV)}	1473 A				
V _{DRM} /V _{RRM}	1200 V, 1600 V, 1800 V, 2000 V, 2200 V, 2400 V, 2600 V				
V _{TM}	1.80 V				
I _{GT}	100 mA				
T _J	-40 °C to 125 °C				

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey PUK
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

Pb-free

RoHS

TYPICAL APPLICATIONS

- DC motor controls
- · Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
,		1473	Α			
I _{T(AV)}	T _{hs}	55	°C			
1		2913	A			
I _T (RMS)	T _{hs}	25	°C			
	50 Hz	20.0	۸			
ITSM	60 Hz	21.2	Α			
l²t	50 Hz	2000	kA ² s			
	60 Hz	1865	KA-S			
I ² √t		20 000	kA²√s			
V _{DRM} /V _{RRM}	Range	1200 to 2600	V			
tq	Typical	300	μs			
T _J	Range	-40 to 125	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J = 125 °C mA				
	12	1200	1300					
	16	1600	1700					
	18	1800	1900					
VS-ST1000CK	20	2000	2100	100				
	22	2200	2300					
	24	2400	2500					
	26	2600	2700					



ABSOLUTE MAXIMUM RATINGS	S					
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	L	180° condu	180° conduction, half sine wave			Α
at heatsink temperature	I _{T(AV)}	Double side	e (single side) co	ooled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink temp	erature double side cooled	6540	Α
		t = 10 ms	No voltage		20.0	
Maximum peak, one-cycle,	L	t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	21.2	kA kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		17.0	
		t = 8.3 ms	reapplied		18.1	
Maximum I ² t for fusing	l ² t	t = 10 ms	No voltage reapplied		2000	
		t = 8.3 ms			1865	
		t = 10 ms			1445	
		t = 8.3 ms	reapplied		1360	
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to	o 10 ms, no vol	age reapplied	20 000	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.950	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			1.024	V
Low level value of on-state slope resistance	r _{t1}	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.283	~ 0
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.265	mΩ
Maximum on-state voltage drop	V_{TM}	$I_{pk} = 3000 \text{ A}, T_J = 125 ^{\circ}\text{C}, t_p = 10 \text{ ms sine pulse}$			1.80	V
Maximum holding current	I _H				600	A
Typical latching current	Ι _L	T _J = 25 °C, anode supply 12 V resistive load			1000	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.9	0
Typical turn-off time	t _q	$I_{TM} = 550 \text{ A, } T_J = T_J \text{ maximum, dl/dt} = 40 \text{ A/}\mu\text{s,}$ $V_R = 50 \text{ V, dV/dt} = 20 \text{ V/}\mu\text{s, gate 0 V 100 }\Omega, t_p = 500 \mu\text{s}$	300	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA



TRIGGERING									
PARAMETER	SYMBOL	TEGT CONDITIONS			VALUES				
PARAMETER	STIVIBUL	"=	ST CONDITIONS	TYP.	MAX.	UNITS			
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum.	, t _p ≤ 5 ms	16		w			
Maximum peak average gate power	P _{G(AV)}	$T_J = T_J$ maximum.	, f = 50 Hz, d% = 50	3	3	VV			
Maximum peak positive gate current	I _{GM}			3.	.0	Α			
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J \text{ maximum}$	$T_J = T_J$ maximum, $t_p \le 5$ ms			$T_J = T_J$ maximum, $t_p \le 5$ ms		0	V
Maximum peak negative gate voltage	- V _{GM}				.0]			
	I _{GT}	T _J = -40 °C	Maximum required gate trigger/	200	-				
DC gate current required to trigger		T _J = 25 °C		100	200	mA			
		T _J = 125 °C	current/voltage are the lowest	50	-	1			
		T _J = -40 °C	value which will trigger all units	1.4	-				
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 V anode to cathode applied	1.1	3.0	V			
T _J = 125 °C		0.9	-						
DC gate current not to trigger	I _{GD}	T T manyimay ma	Maximum gate current/voltage not to trigger is the maximum	1	0	mA			
DC gate voltage not to trigger	V _{GD}	$T_J = T_J$ maximum	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V			

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating temperature range	T_{J}		-40 to 125	°C		
Maximum storage temperature range	T _{Stg}		-40 to 150			
Maximum thermal resistance,		DC operation single side cooled	0.042			
junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.021	K/W		
Maximum thermal resistance,	Б	DC operation single side cooled 0.006		IV VV		
case to heatsink	R _{thC-hs}	DC operation double side cooled	0.003			
Mounting force, ± 10 %			24 500	N		
Wedning force, ± 10 /0			(2500)	(kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet	A-24 (K-P	UK)		

△R _{thJC} CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TECT COMPLETIONS	UNITS	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.003	0.003	0.002	0.002			
120°	0.004	0.004	0.004	0.004	T _J = T _J maximum		
90°	0.005	0.005	0.005	0.005		K/W	
60°	0.007	0.007	0.007	0.007			
30°	0.012	0.012	0.012	0.012			

Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

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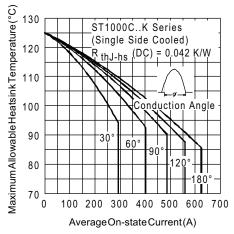


Fig. 1 - Current Ratings Characteristics

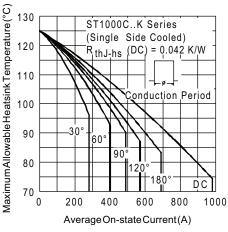


Fig. 2 - Current Ratings Characteristics

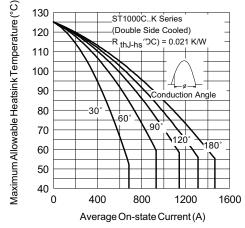


Fig. 3 - Current Ratings Characteristics

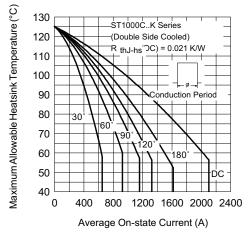


Fig. 4 - Current Ratings Characteristics

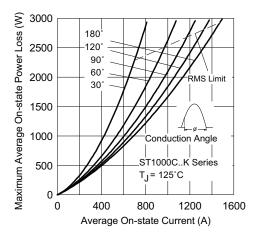


Fig. 5 - On-State Power Loss Characteristics

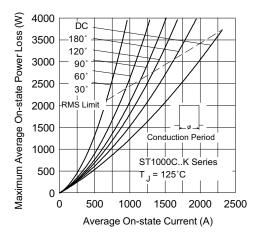
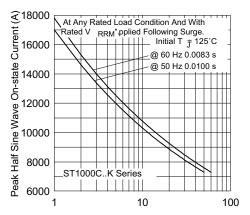


Fig. 6 - On-State Power Loss Characteristics



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Number Of Equal Amplitude Half Cycle Current Pulses (N)

Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

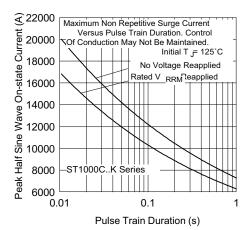


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

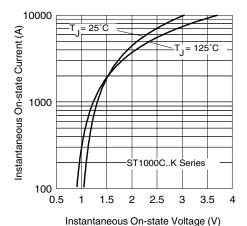


Fig. 9 - On-State Voltage Drop Characteristics

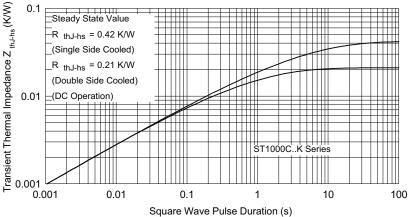


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

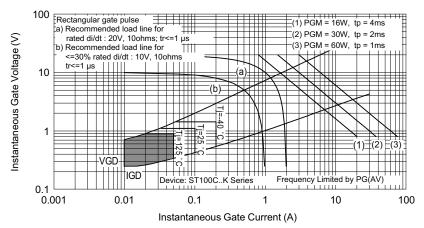
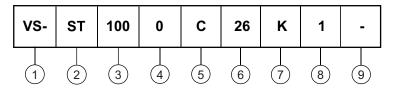


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Thyristor

Essential part number

4 - 0 = Converter grade

5 - C = Ceramic PUK

Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

7 - K = PUK case A-24 (K-PUK)

8 - 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = Eyelet terminals (gate and auxiliary cathode soldered leads)

3 = Fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

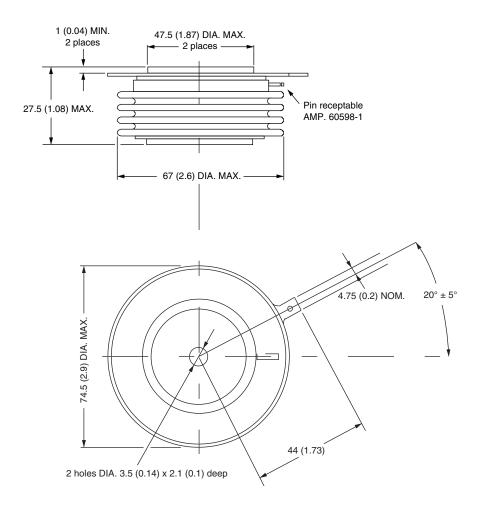
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			



A-24 (K-PUK)

DIMENSIONS in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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